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ABSTRACT OF THE DISCLOSURE

In a semiconductor laser device having a quantum well active layer, an undoped thin spacer layer is formed
5 between an undoped optical guide layer and a p-type cladding layer. The thickness of the spacer layer is preferably 5 nm or more but less than 10 nm. The spacer layer absorbs impurities diffusing thereinto from the p-type cladding layer. Thus, the dopant is prevented from
10 being diffused into the undoped optical guide layer.